

UNITED STATES PATENT AND TRADEMARK OFFICE



UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Viginia 22313-1450 www.nspto.gov

APPLICATION NO. FILING DATE		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/050,182 03/26/1998		HIDETO OHNUMA	07977/242001 6531	
•	590 07/14/2003			
	IARDSON, PC A VILLAGE DRIVE	EXAMINER		
SUITE 500		KUNEMUND, ROBERT M		
SAN DIEGO, O	CA 92122		ART UNIT	PAPER NUMBER
			1765	70
			DATE MAILED: 07/14/2003	16

Please find below and/or attached an Office communication concerning this application or proceeding.

t.,				Application No	D	Applicant(s)	
	0.65	Action Summary	09/050,182		OHNUMA ET AL.		
	Offic A			Examiner		Art Unit	
				Robert M Kune		1765	
Pen a lor	Reply	G DATE fthis commu					ss
- Extens - Extens - If the pr - If NO p - Failure - Any rep	AILING DAI ions of time may b X (6) MONTHS fre eriod for reply spe eriod for reply is s to reply within the ally received by the	ATUTORY PERIOD F E OF THIS COMMUN he available under the provisions om the mailing date of this com- cified above is less than thirty (a pecified above, the maximum is set or extended period for repl- Office later than three months timent. See 37 CFR 1.704(b).	IICATION. s of 37 CFR 1.13 munication. 30) days, a reply tatutory period wi	6(a). In no event, how within the statutory mill apply and will expire cause the application	vever, may a reply be tim inimum of thirty (30) days s SIX (6) MONTHS from	nely filed s will be considered timely. the mailing date of this commo	unication.
1)⊠	Responsive	to communication(s) f	iled on <u>05 M</u>	lay 2003 .			
2a) ☐	This action is	S FINAL.	2b)⊠ This	s action is non-	final.		
'	Since this ap closed in acc n of Claims	pplication is in conditio cordance with the prac	n for allowar tice under <i>E</i>	nce except for f Ex parte Quayle	omal matters, pr , 1935 C.D. 11, 4	osecution as to the m 53 O.G. 213.	erits is
4)⊠ C	laim(s) <u>1-11</u>	<u>15</u> is/are pending in the	e application	١.			
48	a) Of the abo	ve claim(s) <u>60-74</u> is/a	re withdrawr	n from consider	ation.		
5)□ C	laim(s)	_ is/are allowed.					
6)⊠ C	laim(s) <u>1-59</u>	<i>and 75-115</i> is/are reje	ected.				
		_ is/are objected to.					
		_ are subject to restric	ction and/or	election require	ement		
Application	n Papers	•		-			
9)□ Th	e specification	on is objected to by the	e Examiner.				
10)□ Th	e drawing(s)	filed on is/are:	a) accept	ed or b) object	ted to by the Exan	niner.	
		not request that any obj					
		drawing correction filed					,
		orrected drawings are re				-	
12)∐ Th	e oath or de	claration is objected to	by the Exa	miner.			
Priority und	der 35 U.S.C	c. §§ 119 and 120					
13)∐ A∈	cknowledgm	ent is made of a claim	for foreign p	oriority under 3	5 U.S.C. § 119(a)	-(d) or (f).	
		ome * c) None of:			. , ,	, , ,	
1.	☐ Certified	copies of the priority	documents	have been rece	eived.		
2.		copies of the priority				n No.	
	☐ Copies o appl	of the certified copies of ication from the Intern d detailed Office action	of the priority ational Bure	y documents ha au (PCT Rule 1	ave been received	I in this National Stag	e
		nt is made of a claim fo					lication)
a) [The transla	ation of the foreign lan nt is made of a claim fo	guage provi	sional application	on has been rece	ived.	noutiony.
Attachment(s)				, , ,			
2) Notice of	References Cit Draftsperson's on Disclosure S	red (PTO-892) Patent Drawing Review (P statement(s) (PTO-1449) Pa	TO-948) iper No(s)	4)	Interview Summary (Notice of Informal Pa Other:	PTO-413) Paper No(s) tent Application (PTO-152	· ·
S. Patent and Trader	nark Office						

Page 2

Application/Control Number: 90/050,182

Art Unit: 1765

The Rejections

The nonstatutory double patenting rejection is based on a judicially created doctrine grounded in public policy (a policy reflected in the statute) so as to prevent the unjustified or improper timewise extension of the "right to exclude" granted by a patent and to prevent possible harassment by multiple assignees. See *In re Goodman*, 11 F.3d 1046, 29 USPQ2d 2010 (Fed. Cir. 1993); *In re Longi*, 759 F.2d 887, 225 USPQ 645 (Fed. Cir. 1985); *In re Van Ornum*, 686 F.2d 937, 214 USPQ 761 (CCPA 1982); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970); and, *In re Thorington*, 418 F.2d 528, 163 USPQ 644 (CCPA 1969).

A timely filed terminal disclaimer in compliance with 37 CFR 1.321© may be used to overcome an actual or provisional rejection based on a nonstatutory double patenting ground provided the conflicting application or patent is shown to be commonly owned with this application. See 37 CFR 1.130(b).

Effective January 1, 1994, a registered attorney or agent of record may sign a terminal disclaimer. A terminal disclaimer signed by the assignee must fully comply with 37 CFR 3.73(b).

Claims 1 to 59 and 76 to 115 are rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims 1-31 of U.S. Patent No. 5,700,333. Although the conflicting claims are not identical, they are not patentably distinct from each other because the difference is the device formed and heating. However, in the absence of unobvious results, it would have been obvious to one of ordinary skill in the art to determine

Page 3

Application/Control Number: 90/050,182

Art Unit: 1765

through routine experimentation the optimum, operable device formed as the instant claims form any device and heating in order to decrease heating time.

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103© and potential 35 U.S.C. 102(f) or (g) prior art under 35 U.S.C. 103(a).

Claims 1 to 16, 76, 77, 82 to 108, and 112 to 115 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yamazaki et al (5,700,333)...

The Yamazaki et al reference teaches a method of device formation. On a substrate, a layer of amorphous silicon is deposited and then catalysts are placed in contact with the silicon. The silicon is heated in order to crystallize the silicon. Then a gettering agent is added to the silicon layer. Then the structure is reheated to remove the catalyst. The second heating step is around 550°c, note entire reference. The sole difference between the instant claims and the prior

Page 4

Application/Control Number: 90/050,182

Art Unit: 1765

art is the device formed. However, in the absence of unobvious results, it would have been obvious to one of ordinary skill in the art to determine through routine experimentation the optimum, operable types of devices made in the Yamazaki et al reference in order to create devices with low impurity silicon layer.

Claims 17 to 59, 75, 78 to 81 and 109 to 111 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yamazaki et al (5,700,333) in view of Zhang et al (5,569,936)

The Yamazaki et al reference is relied on for the same reasons as stated, supra, and differs from the instant claims in the use of lasers to crystallize the silicon. However, the Zhang et al reference teaches catalyst crystallization of amorphous silicon by using lasers, note figures. It would have been obvious to one of ordinary skill in the art to modify the Yamazaki et al reference by the teachings of the Zhang et al reference to use lasers in order to decrease the time of crystallization.

Response to Applicants' Arguments

Applicant's arguments filed September 11, 2002 have been fully considered but they are not persuasive.

Applicants' argument concerning the gettering in view of the references is noted. However, the Yamazaki reference claims gettering a region or layer claim 1, this means that an area or patterning of the gettering metal is found in the reference. If there is a claimed limitation of a layer and a region, the region cannot be considered an entire layer. Also, at col 6 of the Yamazaki et al reference, it is taught to remove the areas, not layer, where the catalyst has been

Art Unit: 1765

gettered to the metal. This removal would inherently leave islands. The patent does specifically state in col. 6 that areas or regions are treated. It does not state treating the entire area. In fact, the patent states the crystal is damaged in the region of phosphorus. It does not state that the entire layer is damaged. Thus, when the reference states region on of ordinary skill in the art would not read that to be the entire layer.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Robert Kunemund whose telephone number is (703) 308-1091. The examiner can normally be reached on Monday through Friday from 7:00 to 3:30.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Ben Utech, can be reached on (703) 308-3836. The fax phone number for this Group is (703) 305-6357.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the Group receptionist whose telephone number is (703) 308-0661.

ROBERT KUNEMUND PRIMARY EXAMINER

RMK

July 8, 2003